

H-Sensors and Fusion Work at SNL-CA

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Useful discussions with Peter Stangeby (Univ. of Toronto)
And Bob Bastasz (SNL-CA retired)

Outline

- Overview of Hydrogen Work
- Details of Fusion Program on PSI
- Motivation for Atomic Hydrogen Measurements
- Pd-MOS Hydrogen Sensors

Tritium Focus Group Meeting, INL, September 23-25, 2014



Sandia National Laboratories is a multi program laboratory managed and operated by Sandia Corporation, a wholly owned subsidiary of Lockheed Martin Corporation, for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-AC04-94AL85000.



Building a science-based understanding of hydrogen (and helium) behavior in materials

- High pressure hydrogen storage for Gas Transfer Systems and hydrogen / fuel cell industry →
 - Embrittlement, permeation, trapping, microstructural effects, corrosion, Codes and Standards (H² safety)
- Metal hydride studies for hydrogen storage →
 - He trapping from T decay, film adhesion, aging, new materials
- Tritium production (TPBAR)
 - T migration in a complex materials environment
- Plasma-surface interactions (PSI) studies needed for magnetic fusion energy

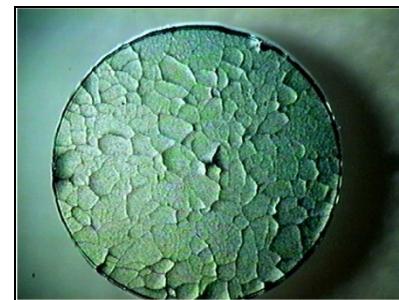
R&D efforts span a number of applied programs at SNL-CA



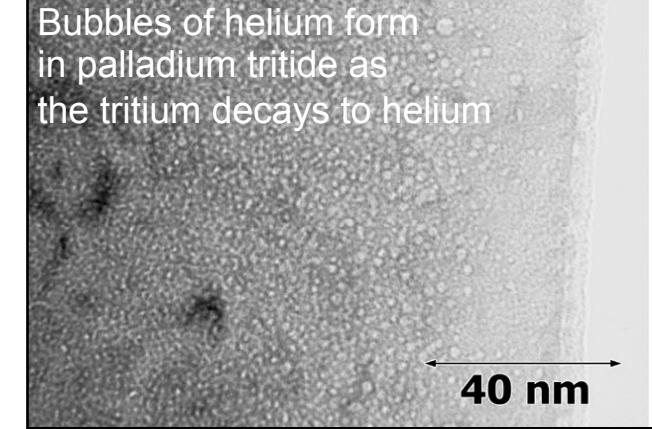
Austenitic stainless steel



Cr-Mo ferritic steel, <45 MPa



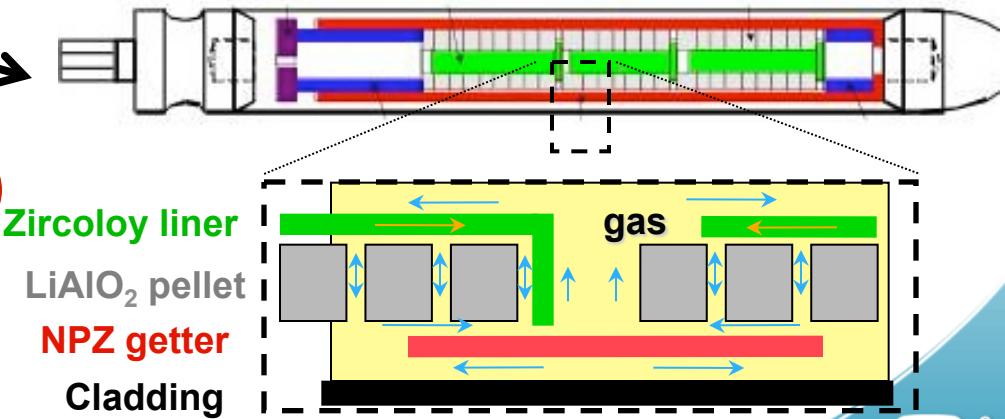
Bonding in n-tube films



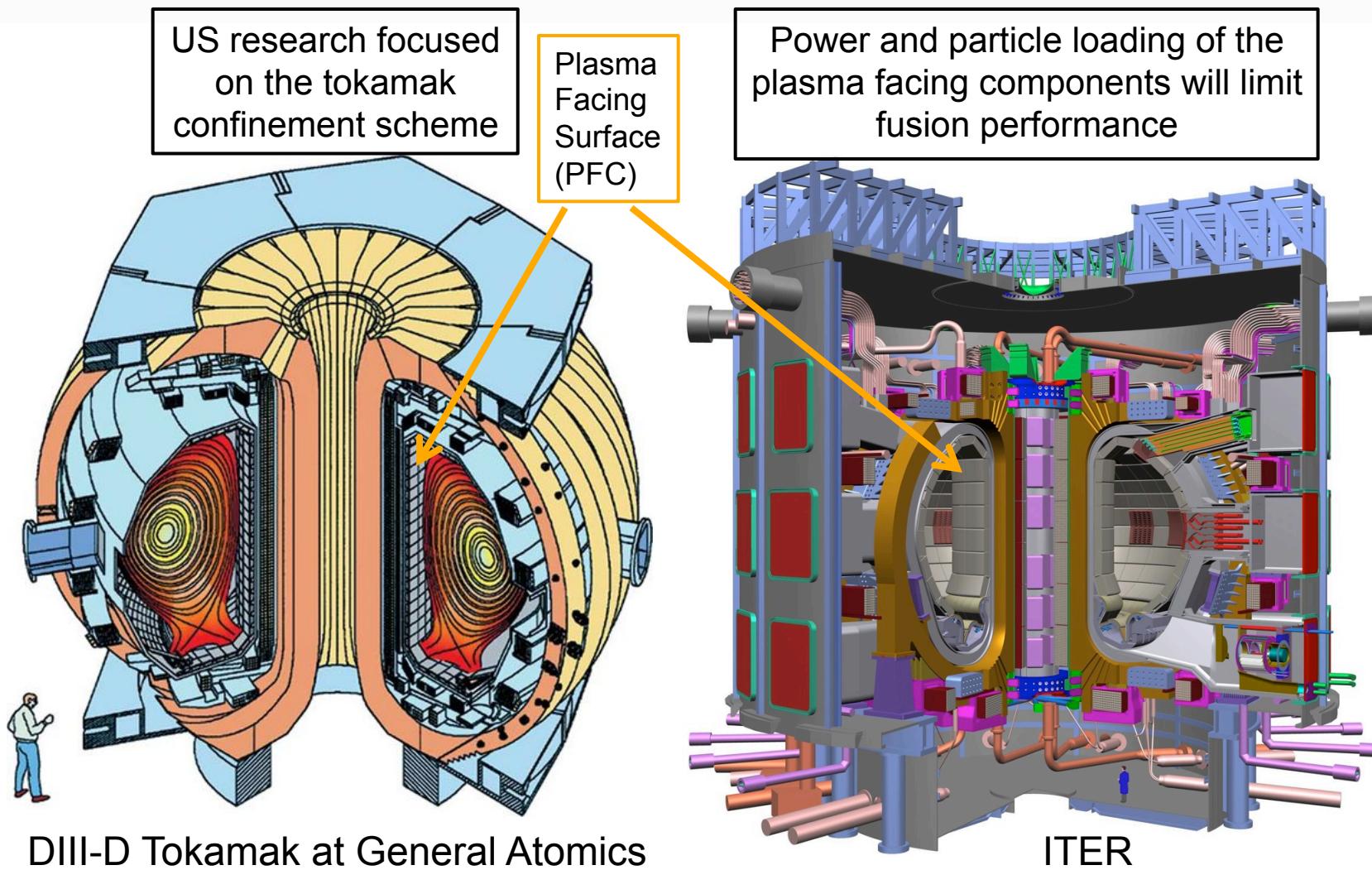
Bubbles of helium form in palladium tritide as the tritium decays to helium

40 nm

Tritium Producing Burnable Absorber Rods



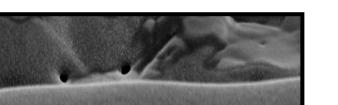
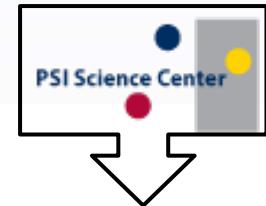
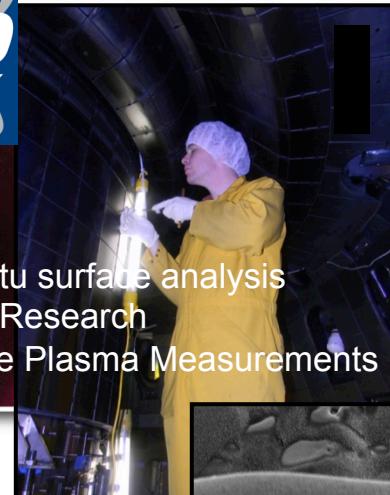
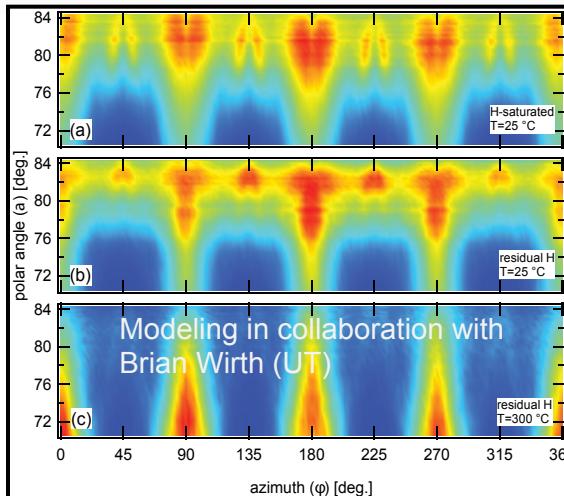
Magnetic fusion energy research



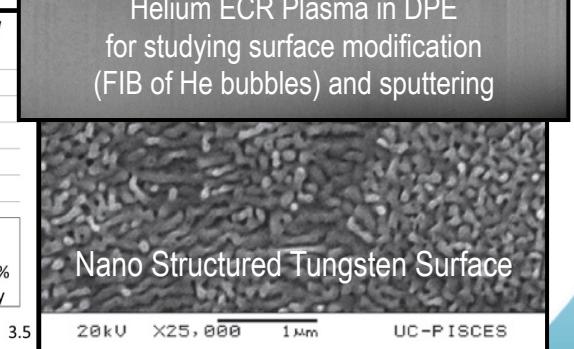
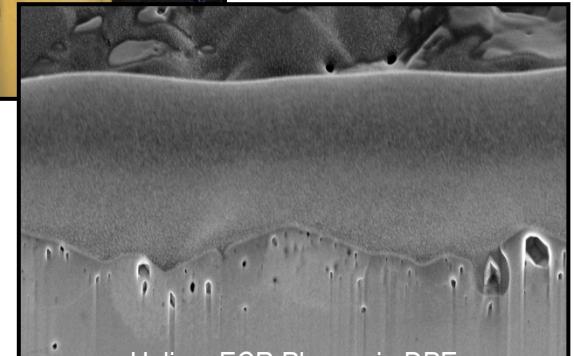
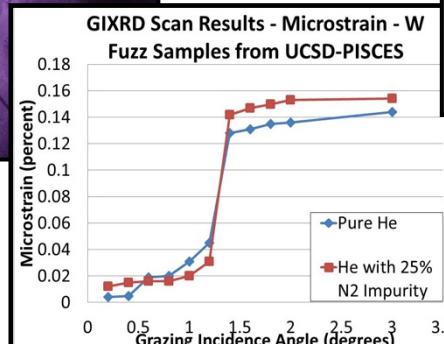
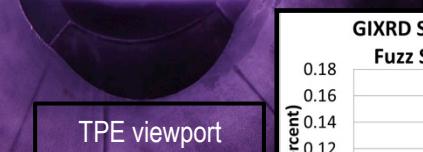
Greenwald report, ReNeW study, and OFES all agree on importance of PFC/PFI

SNL-CA PSI Science Center Research (FY10-14)

Fundamental surface science of H effects in ARIES



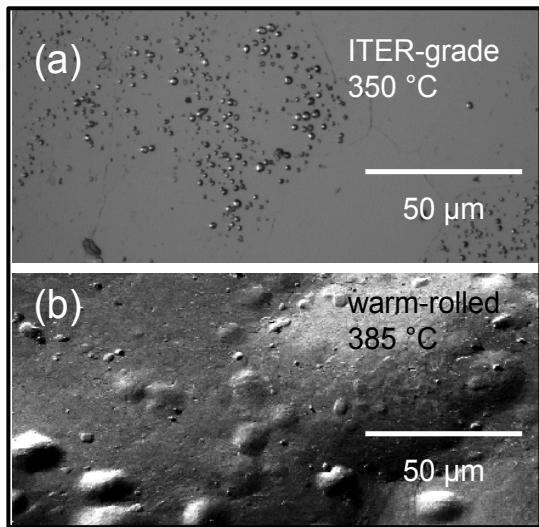
Tritium Plasma Experiment at INL



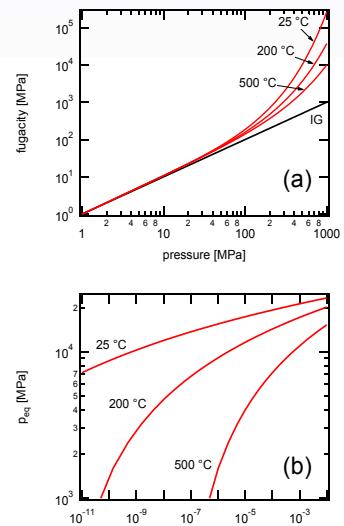
The PSI SC efforts are heavily leveraged with our base program funding



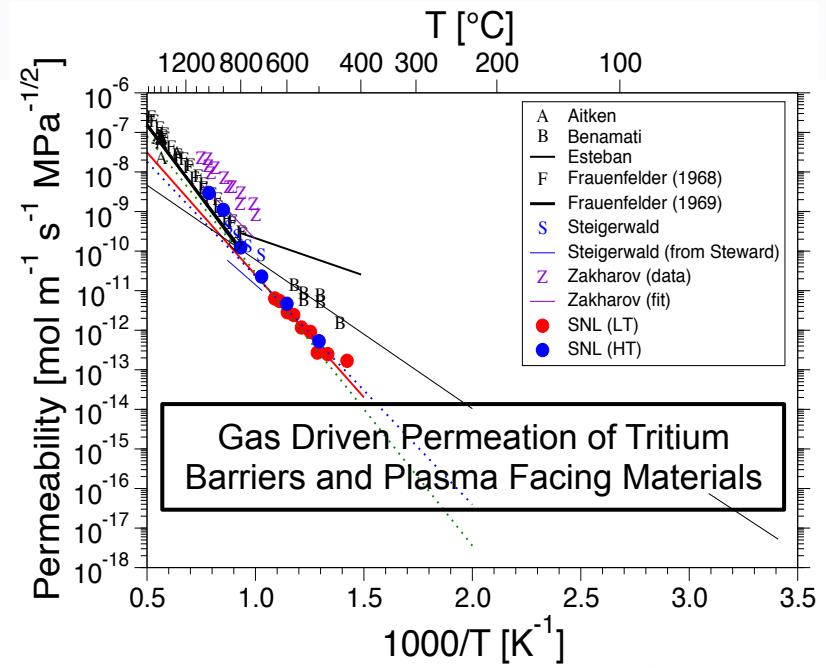
SNL-CA base program (Technology & DIII-D)



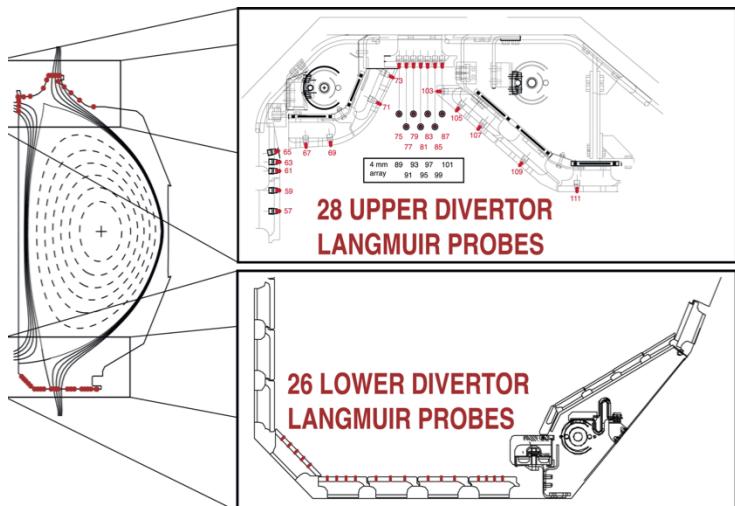
Hydrogen induced blistering of W



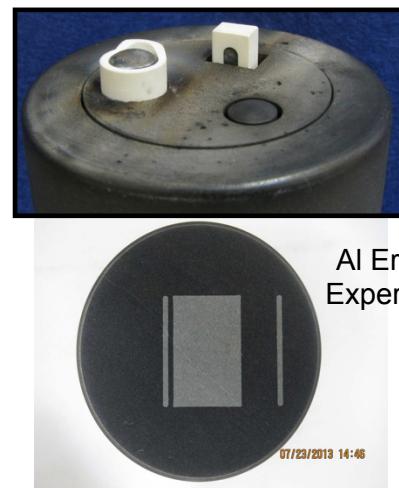
Equilibrium Pressure
From Bubble Model



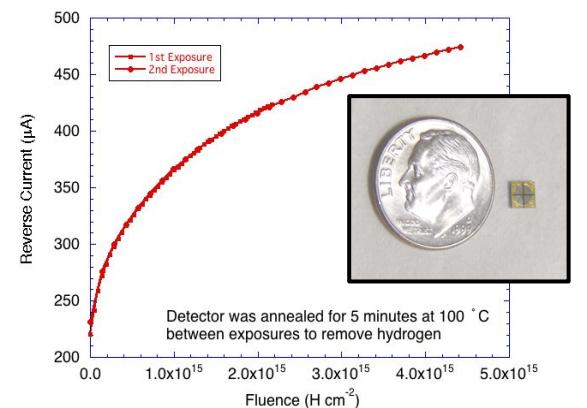
Gas Driven Permeation of Tritium
Barriers and Plasma Facing Materials



Edge Plasma Characterization in DIII-D



Plasma Measurements and
Erosion/Redeposition Experiments
on DiMES (DIII-D)



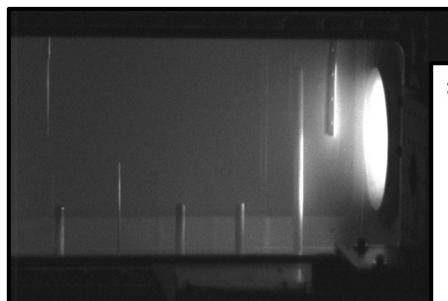
Hydrogen Microsensor Development



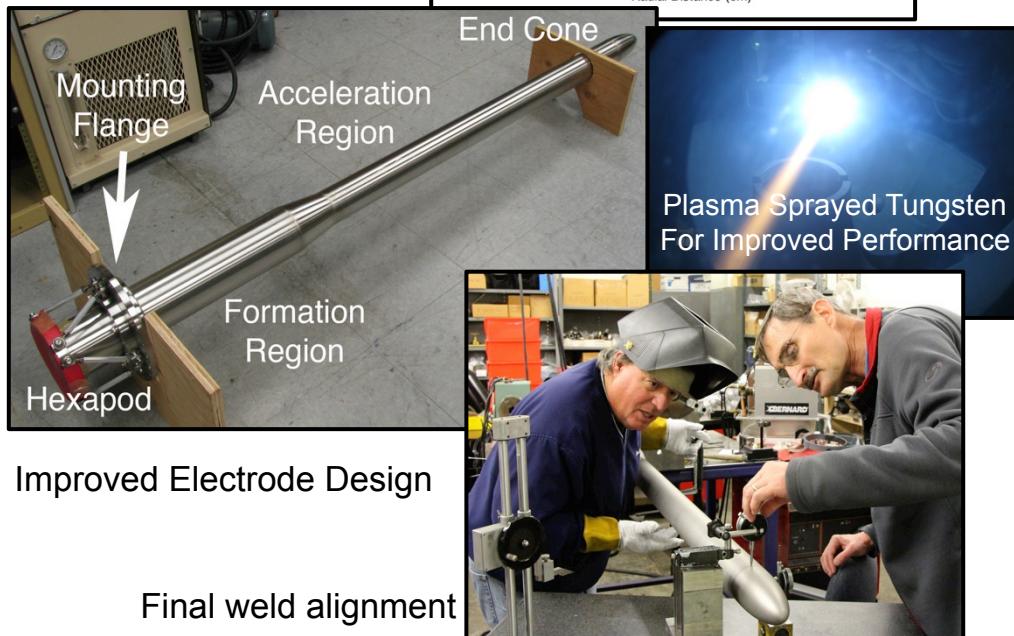
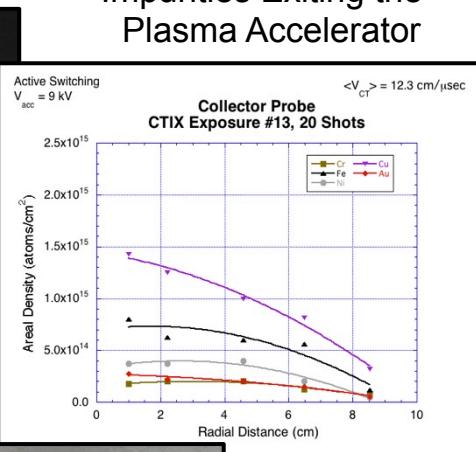
Other fusion research at SNL-CA



Plasma Surface Interactions in the Compact Toroid Injection Experiment (started in FY10)



Collector Probes in CTIX



Improved Electrode Design

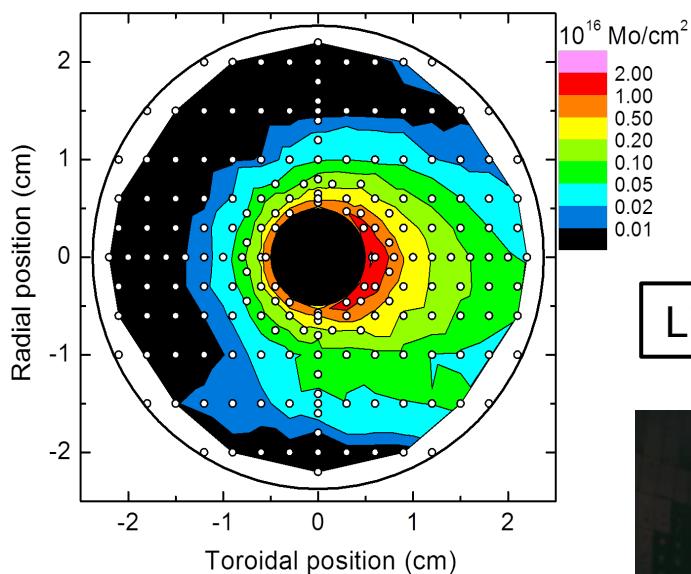


Sandia Ion Beam Laboratory (NM)



DiMES experiments on DIII-D

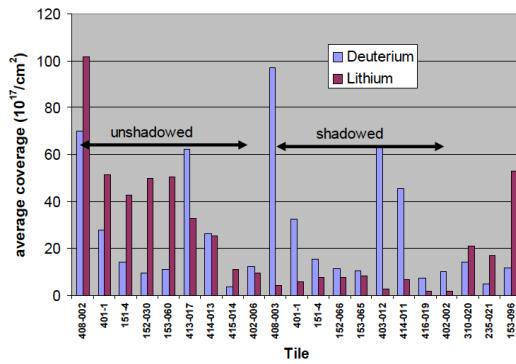
Molybdenum erosion 0.5 nm/s



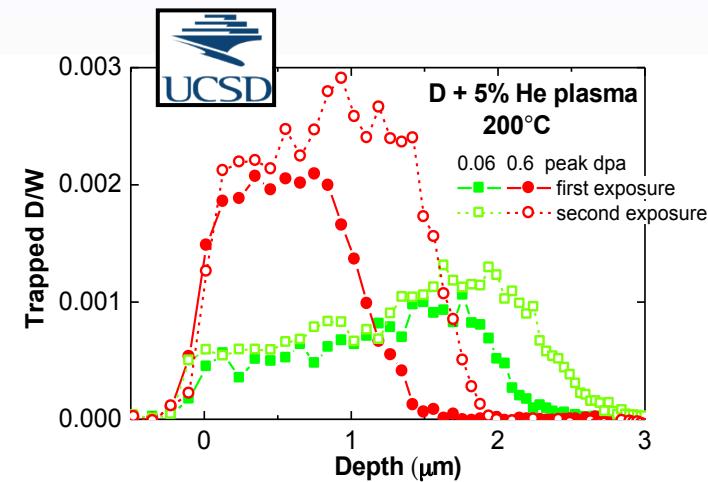
19% redeposited locally
with $\lambda=2.3 \text{ mm}$



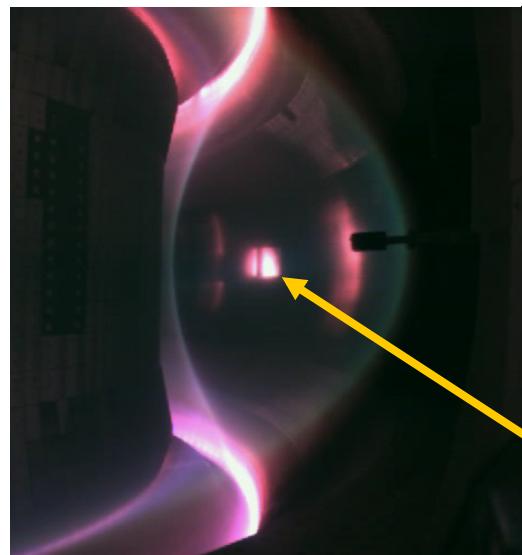
Average coverage of Li & D on each tile



Li and D coverage on NSTX tiles



Deuterium trapping studies on damaged tungsten in PISCES



EAST/Mapes Material Erosion Experiment



US fusion program has a major focus studying plasma-material interactions (including erosion)

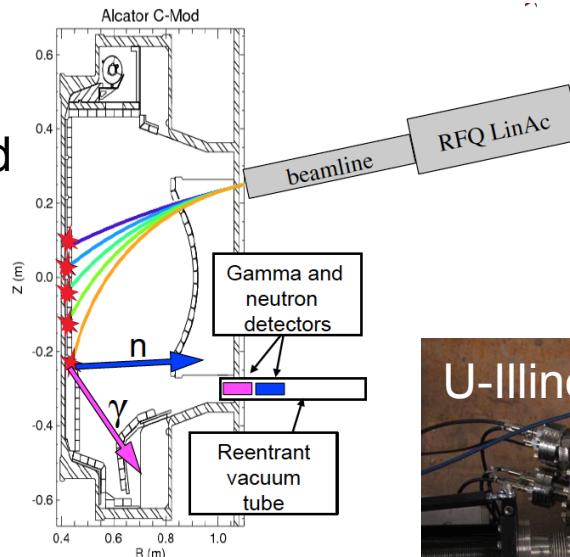
■ DIII-D

- DiMES (divertor) and MiMES (first wall) experiments provide erosion / redeposition data for plasma-material interaction model validation (REDEP/ WBC-ITMC code)



■ Alcator C-Mod

- High Z erosion and redeposition studied using a dedicated ion beam facility
- AIMS: Accelerator-based In-situ Materials Surveillance (compact RFQ LinAc injects 0.9 MeV D+)



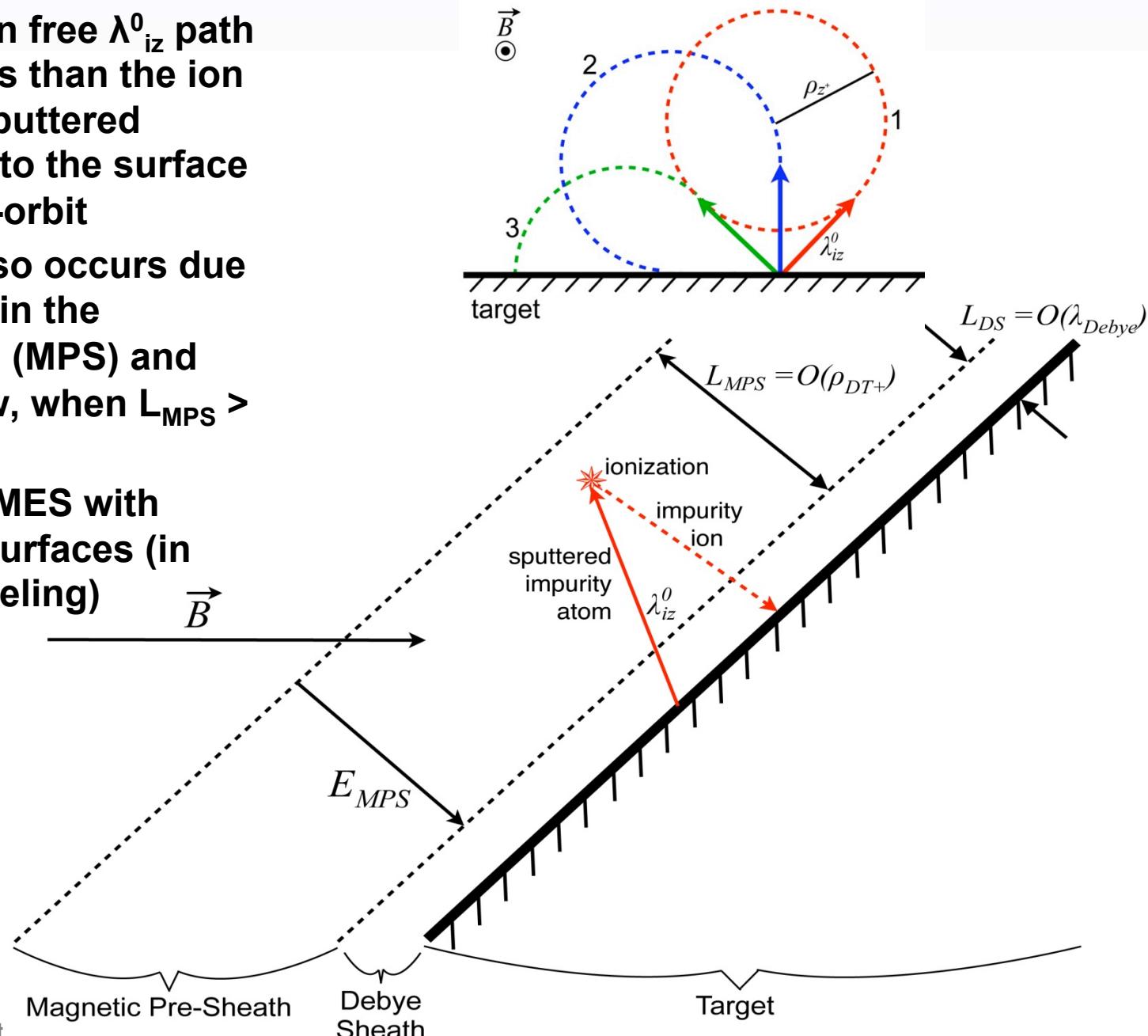
■ NSTX-U

- MAPP: Material Analysis and Particle Probe (sample exposure with in-situ TDS, XPS, LEIIS, DRS)

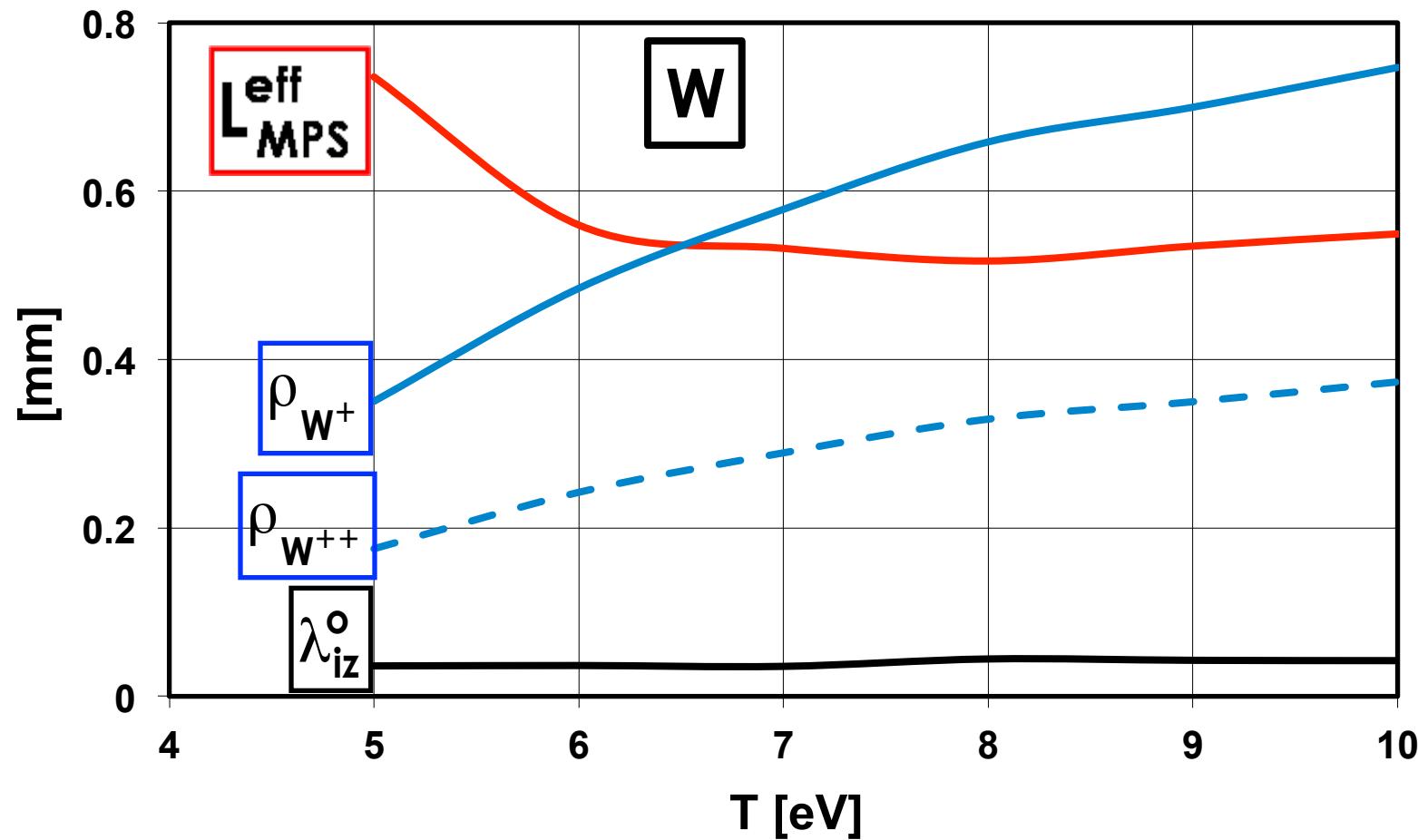


Prompt redeposition in the magnetized sheath of the divertor is expected to reduce net erosion

- If the ionization mean free λ_{iz}^0 path is comparable or less than the ion Larmor radius ρ_{z+} , sputtered impurity ions return to the surface during the first gyro-orbit
- Fast redeposition also occurs due to the strong E-field in the magnetic pre-sheath (MPS) and friction with fast flow, when $L_{MPS} > \lambda_{iz}^0$
- Demonstrated on DiMES with tungsten and moly surfaces (in agreement with modeling)



For tungsten, prompt deposition should be effective in DT devices via both strong MPS forces and large ρ_w



ITER case with $n_e = 10^{21} \text{ m}^{-3}$, $B = 5 \text{ T}$

Courtesy of P. Stangeby

Prompt deposition *is not* expected at the first wall

- Much lower far scrape off layer (SOL) plasma density ($\sim x10^{-3}$) will result in longer ionization mean free path λ^0_i
 - Sputtered wall neutrals will penetrate into the far SOL and experience migration towards the divertor
- The sputtering can be due to either plasma ions or charge exchange (c-x) neutrals
- While several efforts to characterize the first wall c-x flux occurred during the 80's / 90's, no current investigations exist on US tokamaks
 - LENA (Low Energy Neutral Analyzer): PLT, ASDEX, Alcator C-Mod (installed only)
 - CRP (Carbon Resistance Probe): TMX-U, PLT, ASDEX, TFTR
 - Pd-MOS H-sensors (Palladium Metal-Oxide-Semiconductor)
 - Diode type: ZT-40M and TFTR
 - Capacitance type: DIII-D, NSTX
- Is the flux of c-x neutrals important in FW erosion? What is the poloidal and toroidal distribution of the c-x flux? How will c-x induced erosion scale in future devices?
- Simple estimate on next viewgraph: physical sputtering of T using $E=300$ eV (Eckstein 2002), normal incidence yield doubled to account for surface roughness, no sputtering by other plasma or wall species, $P_{cx} = 0.05 P_{heat}$ (\sim Kukushkin for ITER)

Rough estimate of c-x induced FW erosion

For 300 eV T° c-x sputtering of walls	P_{heat} [M W]	annual run time [s/year]	beryllium net wall erosion rate [kg/yr]	boron net wall erosion rate [kg/yr]	carbon net wall erosion rate [kg/yr]	tungsten net wall erosion rate [kg/yr]
DIII-D	20	10^4	0.13	0.11	0.08	0.16
JT-60SA	34	10^4	0.22	0.19	0.15	0.27
EAST	24	10^5	1.6	1.2	0.82	1.8
ITER	100	10^6	77 [29*] {60***}	64	44 [53*] {54***}	92 [41*] {46***}
Vulcan	20	10^7	120	100	70	150
FDF	100	10^7	610	500	340	740
Reactor	400	2.5×10^7	6500	5300	3700	7900 [5000**]

* Kukushkin B2-EIRENE calculation

**Lackner

***Behrisch

Courtesy of P. Stangeby



Techniques for measuring c-x flux

■ LENA (Low Energy Neutral Analyzer)

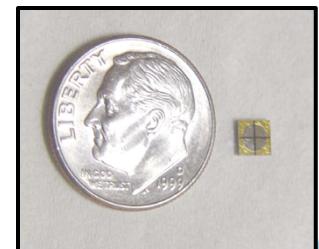
- Pros: provides good time and energy resolution
- Cons: Available at only a few locations (usually one) due to size and complexity

■ CRP (Carbon Resistance Probe)

- Pros: compact and low power device, energy discrimination by array with varying overlayers, good time resolution
- Cons: device saturates permanently at $2 \times 10^{15} \text{ H/cm}^2$

■ Pd-MOS H-sensors (Palladium Metal-Oxide-Semiconductor)

- Pros: compact and low power device, energy discrimination by array with varying overlayers, in-situ reset through heating of device
- Cons: dosimetric (shot by shot), lifetime limited by charge trapping



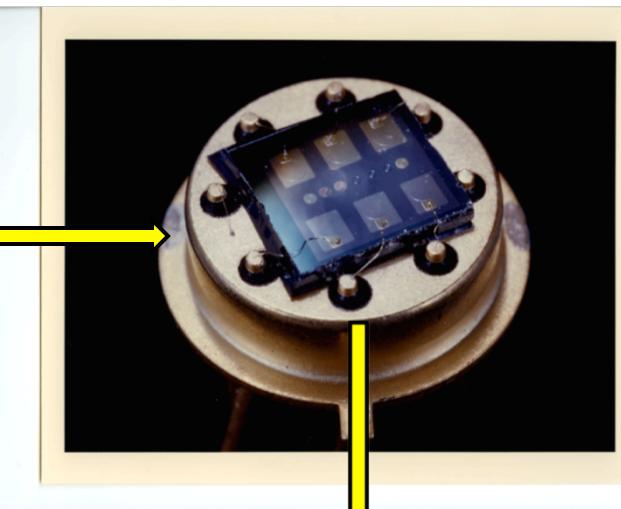
Each device can play a role towards quantifying c-x flux in existing experiments

Pd-MOS sensor use in confinement experiments

- First use on ZT-40M demonstrated dosemetric effect of sensors

R. Bastasz, J. Nucl. Mater. 162-164 (1989) 587.

Work by Bob Bastasz and Bob Hughes

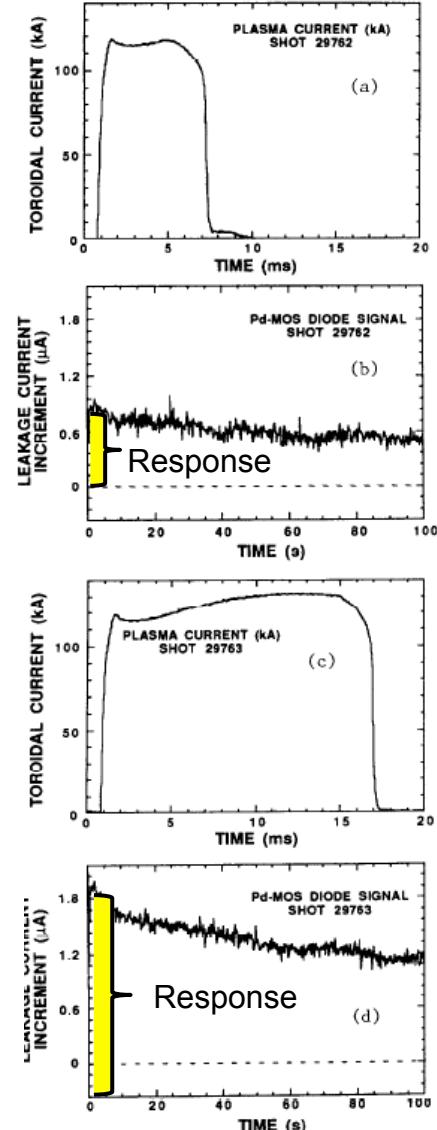
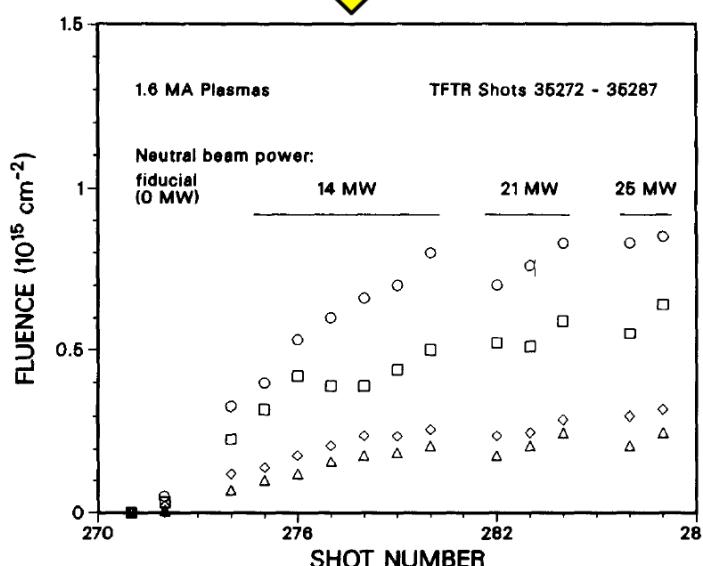


- An array sensor was used on TFTR to demonstrate energy resolving c-x measurement

R. Bastasz, J. Nucl. Mater. 176-177 (1990) 1038.

- Switched to capacitance type detectors for easy of fabrication

- Tests on DIII-D and NSTX were not successful
 - Likely cause: charge production in thick oxide layer due to x-rays or high energy charged particles

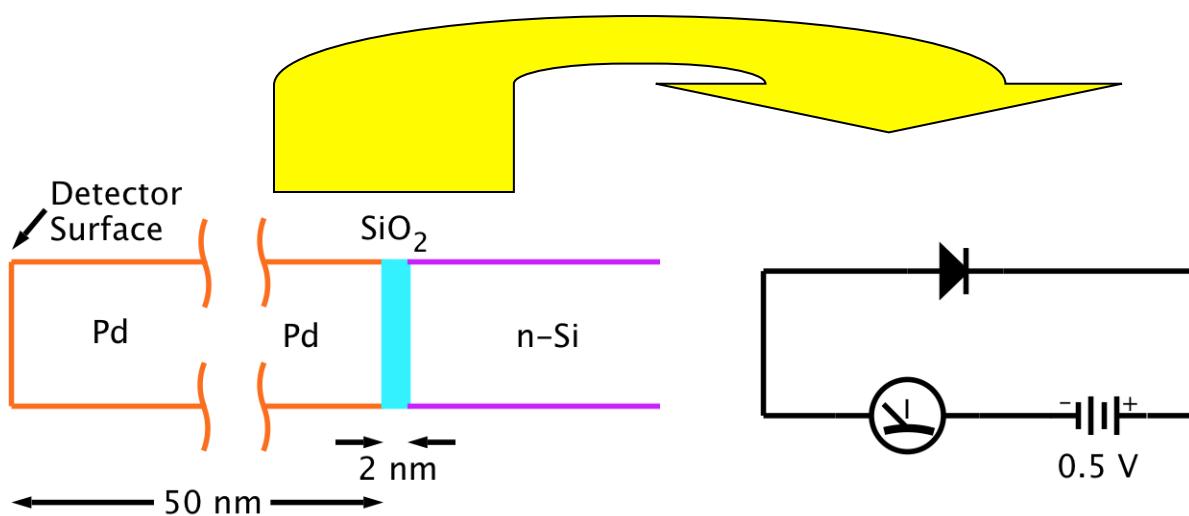


Pd-MOS Schottky diode type H-sensors

- Diode type detectors will limit charge production due to thin tunnel oxide while a thicker Pd coating can protect from high energy particles
- Hydrogen entering the palladium metal diffuses rapidly, filling surface sites at the Pd-tunnel oxide interface, and changing the barrier height of the diode
 - Simple model of current under reverse bias

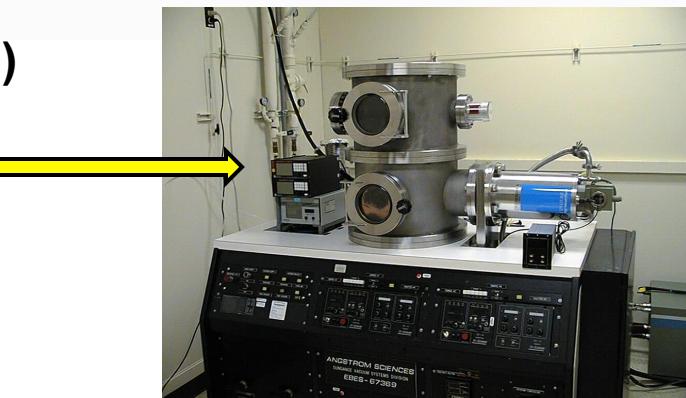
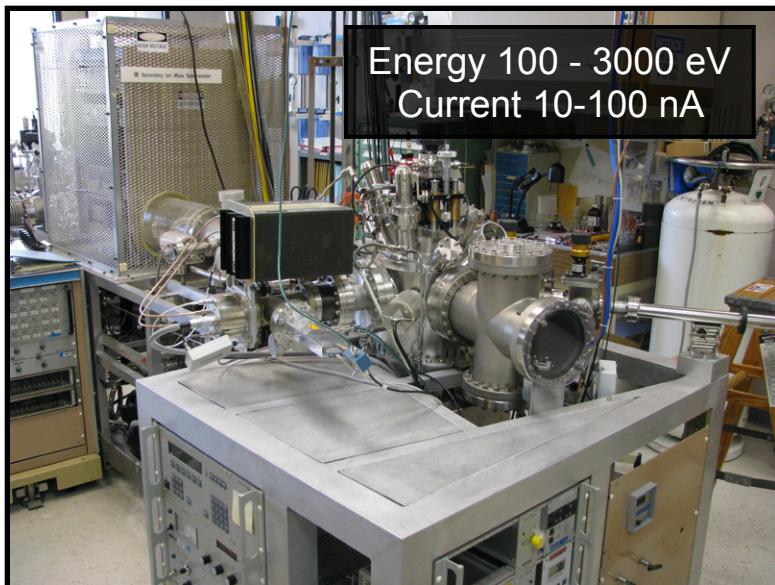
$$I_r = AT^2 \exp[-\phi_b / kT] \quad \phi_b = \phi_m - \chi$$

- A is a factor depending on the device size and applied voltage, T is the temperature, and ϕ_b is the barrier height. ϕ_m is the metal work function and χ is the electron affinity of the silicon. Hydrogen at the interface changes ϕ_m giving a large change in reversed current.

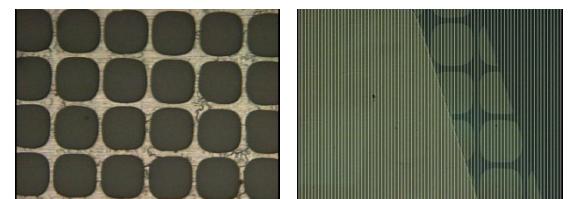


Initial attempts to fabricate rugged Pd-MOS H-sensors

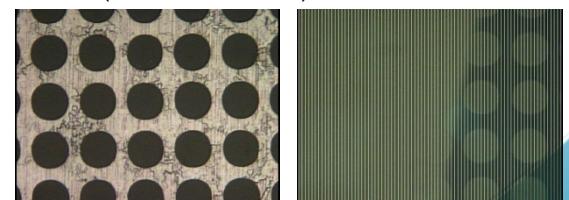
- Wafers were stripped and 2 nm tunnel oxide grown in the MESAfab (silicon fab at SNL-NM)
- Pd films and titanium adhesion grids were deposited at SNL-CA (summer of 2010)
 - Ti used to improve adhesion in the semiconductor industry
- Each wafer produced many sensors (3.6 mm square)
- Sensors were evaluated using a mass and energy filtered ion beam (SNL-CA)



10 keV dual e-beam evaporator used to deposit Pd, Ti, and Au under high vacuum (10^{-6} Torr). Typical deposition rates are 50 Å/s.



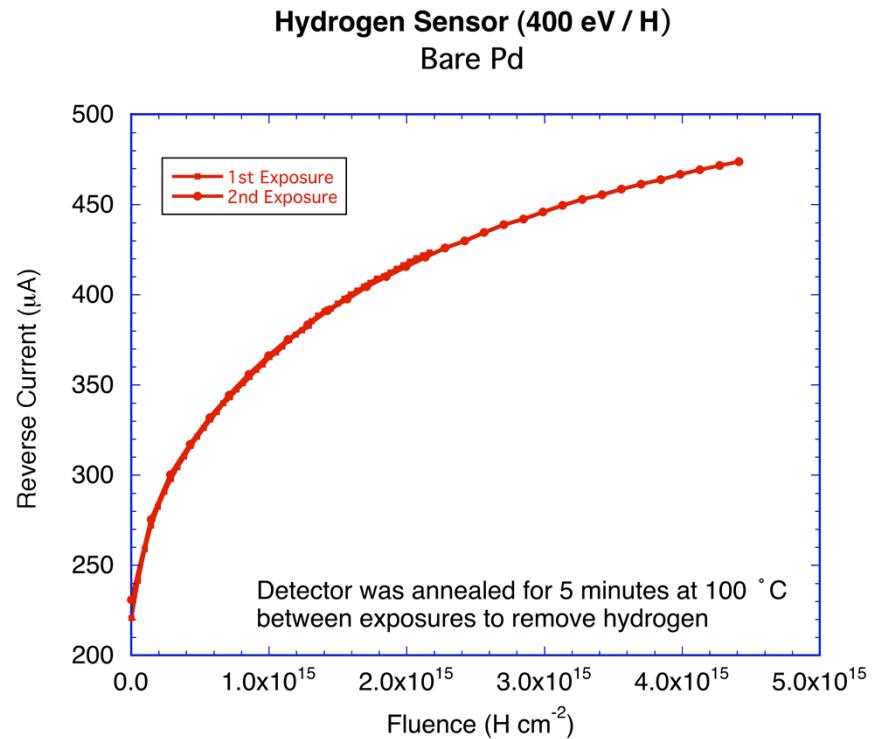
200 Å thick Ti posts at 200 dots/inch (48% active area) and 2000 Å thick Pd



200 Å thick posts at 200 dots/inch (76% active area) and 2000 Å thick Pd

Ti posts unsuccessful, but diode-type H-sensors did exhibit similar behavior to previous detectors

- 20 nm Ti post array was too reactive and shorted the Pd metal-oxide interface
- Bare Pd sensors exhibited good response and reproducibility. Energy sensitivity needs further study.
- Exploring other options which will exploit extensive processing capabilities at the MESAfab
- Development of rugged detectors will require more than the 2010 several-month effort described here
- Leveraging of the MESAfab facility and expertise would require only a modest investment

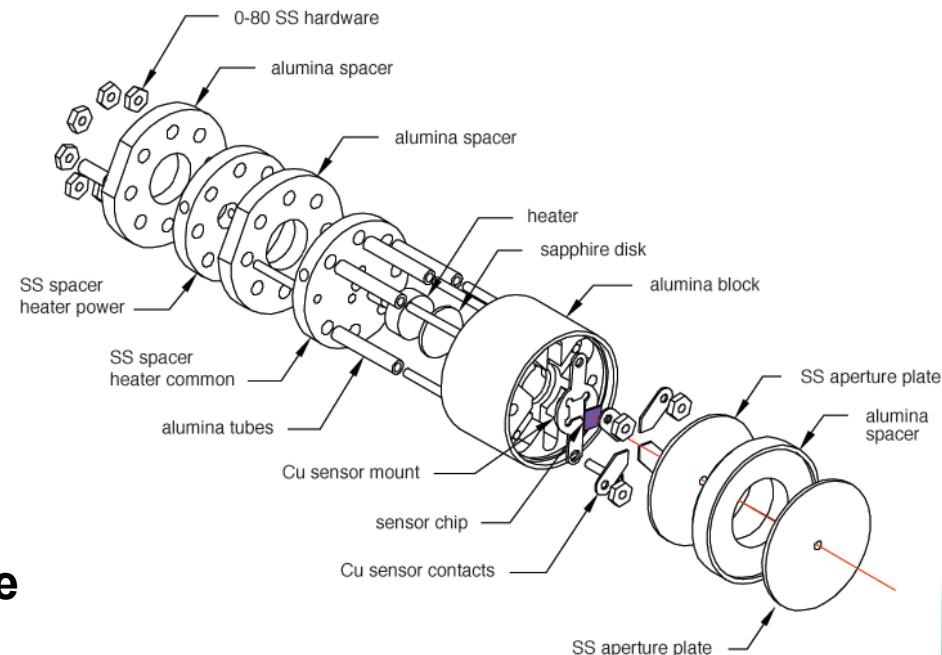


MESAfab Key Fabrication Capabilities

<ul style="list-style-type: none">• Photolithography Processes (Coat/Expose/Develop)• Electron Beam (E-Beam) Lithography• Reactive Ion Etch• Wet Etch/Clean• Oxidation and Diffusion• Thin Films• Chemical Mechanical Polishing (CMP) for planarization• Ion Implantation• Metrology• Deep Reactive Ion Etch (DRIE)	<ul style="list-style-type: none">• Electroplating• Packaging• MEMS Release• Yield Learning• Statistical Process Control• III-V Compound Semiconductor Epitaxial Growth• Mixed-Technology Integration and Processing• 3D Integration• Materials Characterization• Failure Analysis• Wafer Bonding and Thinning
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Summary

- Unlike the divertor, the first wall of tokamaks will not experience prompt redeposition of sputtered material. Thus net erosion will be ~ gross erosion.
- Simple estimates and more complete simulations indicate that charge-exchange sputtering will result in large migration of first wall material in future devices.
- The development of Pd-MOS diode H-sensors would provide a tool that could quantify the poloidal and toroidal charge-exchange flux.
- Combined with the high energy and time resolution of a LENA, arrays of Pd-MOS devices could provide critical data for edge plasma – neutral model validation.



Pd-MOS H-sensor DiMES head

Continued interest at DIII-D and NSTX to evaluate Pd-MOS H-sensors